



INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

Docket Number (Optional)

EIS920040116US1

Application Number

10/710,244

Applicant(s)

Huiling Zhu

Filing Date

06/29/2004

Group Art Unit

2811

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
P6		3,602,841	8-31-71	McGroddy			
		4,665,415	5-12-87	Esaki, et al			
		4,853,076	8-1-89	Tsaur, et al			
		4,855,245	8-8-89	Neppi, et al			
		4,952,524	8-28-90	Lee, et al			

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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
P3		US 2001/0009784 A1	7-26-01	Ma, et al			
		US 2002/0063292 A1	5-30-02	Armstrong, et al			
		US 2002/0074598 A1	6-20-02	Doyle, et al			
		US 2002/0086472	7-4-02	Roberds, et al			

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	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
P2		JP64-76755	03-1989	Japan				

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(Including Author, Title, Date, Pertinent Pages, Etc.)

P4		Kern Rim, et al, "Transconductance Enhancement in Deep Submicron Strained-Si n-MOSFETs". International Electron Devices Meeting, 26, 8, 1, IEEE, September 1998.
P2		Kern Rim, et al, "Characteristics and Device Design of Sub-100 nm Strained Si N- and PMOSFETs." 2002 Symposium on VLSI Technology Digest of Technical Papers, IEEE, pp. 98-99.

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PK		4,958,213	9-18-90	Eklund, et al.			
		5,006,913	4-9-91	Sugahara, et al.			
		5,060,030	10-22-91	Hoke, et al.			
		5,081,513	1-14-92	Jackson, et al.			
		5,108,843	4-28-92	Ohtaka, et al.			

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PK		US 2002/0086497 A1	7-4-02	Kwok			
		US 2002/0090791 A1	7-11-02	Doyle, et al.			
		US 2003/0032261 A1	2-13-03	Yeb, et al.			
		US 2003/0040158 A1	2-27-03	Saltob			

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PK		Gregory Scott, et al., "NMOS Drive Current Reduction Caused by Transistor Layout and Trench Isolation Induced Stress." International Electron Devices Meeting, 34.4.1, IEEE, September 1999.
		F. Ootanka, et al., "A Highly Dense, High-Performance 130nm Node CMOS Technology for Large Scale System-on-a-Chip Application." International Electron Devices Meeting, 23.5.1, IEEE, April 2000.

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R		5,134,085	7-28-92	Gilgen, et al.			
		5,310,446	5-10-94	Konishi, et al.			
		5,354,695	10-11-94	Leedy			
		5,371,399	12-6-94	Burroughes, et al.			
✓		5,391,510	2-21-95	Hsu, et al.			

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R		US 2003/0057184 A1	3-27-03	Yu, et al.			
		US 2003/0067035 A1	4-10-03	Tews, et al.			
		US 2004/0113174 A1	6-17-2004	Chidambarrao et al.			
✓		US 2004/0113217 A1	6-17-2004	Chidambarrao et al.			

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R		Shinya Ito, et al., "Mechanical Stress Effect of Etch-Stop Nitride and Its Impact on Deep Submicron Transistor Design." International Electron Devices Meeting, 10.7.1, IEEE, April 2000.
✓		A. Shimizu, et al., "Local Mechanical-Stress Control (LMC): A New Technique for CMOS-Performance Enhancement." International Electron Devices Meeting, IEEE, March 2001.

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14		5,459,346	10-17-95	Asakawa, et al.			
		5,471,948	12-5-95	Burroughes, et al.			
		5,557,122	9-17-96	Shrivastava, et al.			
		5,561,302	10-1-96	Candelaria			
		5,565,697	10-15-96	Asakawa, et al.			

U.S. PATENT APPLICATION PUBLICATIONS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
13		US 2004/0238914 A1	12-2-2004	Deshpande et al.			
		US 2004/0262784 A1	12-30-2004	Doris et al.			
		US 2005/0040460 A1	2-24-2005	Chidanbarao et al.			
		US 2005/0082634 A1	4-21-2005	Doris et al.			

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OTHER DOCUMENTS

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14		K. Ota, et al., "Novel Locally Strained Channel Technique for High Performance 55nm CMOS." International Electron Devices Meeting, 2.1.1, IEEE, February 2002.					
		G. Zhang, et al., "A New 'Mixed-Mode' Reliability Degradation Mechanism in Advanced Si and SiGe Bipolar Transistors." IEEE Transactions on Electron Devices, vol. 49, no. 12, December 2002, pp. 2151-56.					

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EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILED DATE IF APPROPRIATE
✓		5,571,741	11-5-96	Leedy			
		5,592,007	1-7-97	Leedy			
		5,592,018	1-7-97	Leedy			
		5,670,798	9-23-97	Schetzina			
↓		5,679,965	10-21-97	Schetzina			

U.S. PATENT APPLICATION PUBLICATIONS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILED DATE IF APPROPRIATE
✓		US 2005/0093030 A1	5-5-2005	Doris et al.			
		US 2005/0098829 A1	5-12-2005	Doris et al.			
		US 2005/0106799 A1	5-19-2005	Doris et al.			
↓		US 2005/0145954 A1	7-7-2005	Zhu et al.			

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OTHER DOCUMENTS

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✓		H.S. Momose, et al., "Temperature Dependence of Emitter-Base Reverse Stress Degradation and its Mechanism Analyzed by MOS Structures." Paper 62, pp. 140-143.
✓		C.J. Huang, et al., "Temperature Dependence and Post-Stress Recovery of Hot Electron Degradation Effects in Bipolar Transistors." IEEE 1991 Bipolar Circuits and Technology Meeting 7.5, pp. 170-173.

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R		5,683,934	11-4-97	Candelaria			
		5,840,593	11-24-98	Leedy			
		5,861,651	1-19-99	Brasen, et al.			
		5,880,040	3-9-99	Sun, et al.			
		5,940,716	8-17-99	Jin, et al.			

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EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
R		US 2005/0148146 A1	7-7-2005	Doris et al.			
		US 2005/0194699 A1	9-8-2005	Belvansky et al.			
		US 2005/0235668 A1	10-27-2005	Zhu et al.			
		US 2005/0245017 A1	11-3-2005	Belyansky et al.			

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R		S.R. Sheng, et al., "Degradation and Recovery of SiGe HBTs Following Radiation and Hot-Carrier Stressing." Pp. 14-15.
R		Z. Yang, et al., "Avalanche Current Induced Hot Carrier Degradation in 200 GHz SiGe Heterojunction Bipolar Transistors." Pp. 1-5.

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B		5,940,736	8-17-99	Brady, et al.			
		5,946,559	8-31-99	Leedy			
		5,960,297	9-28-99	Saki			
		5,989,978	11-23-99	Peldous			
		6,008,126	12-28-99	Leedy			

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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
B		US 2006/0060925 A1	3-23-2006	Doris et al.			
		US 2005/0280051 A1	12-22-2005	Chidambarrao et al.			
		US 2005/0282325 A1	12-22-2005	Belyansky et al.			
		US 2006/0027868 A1	2-9-2006	Doris et al.			

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(Including Author, Title, Date, Pertinent Pages, Etc.)

B		H. Li, et al., "Design of W-Band VCOs with High Output Power for Potential Application in 77 GHz Automotive Radar Systems." 2003 IEEE GaAs Digest, pp. 263-66.					
B		H. Wurzer, et al., "Annealing of Degraded npp-Transistors- Mechanisms and Modeling." IEEE Transactions on Electron Devices, vol. 41, no. 4, April 1994, pp. 533-38.					

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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
✓		6,025,280	2-15-00	Brady, et al.			
↓		6,046,464	4-4-00	Schetzina			
		6,066,545	5-23-00	Doshi, et al.			
		6,090,684	7-18-00	Ishitsuka, et al.			
↓		6,107,143	8-22-00	Park, et al.			

U.S. PATENT APPLICATION PUBLICATIONS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
✓		US 2006/0057787 A1	3-16-2006	Doris et al.			

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✓		B. Doyle, et al., "Recovery of Hot-Carrier Damage in Reoxidized Nitrided Oxide MOSFETs." IEEE Electron Device Letters, vol. 13, no. 1, January 1992, pp. 38-40.
↓		H.S. Momose, et al., "Analysis of the Temperature Dependence of Hot-Carrier-Induced Degradation in Bipolar Transistors for Bi-CMOS." IEEE Transactions on Electron Devices, vol. 41, no. 6, June 1994, pp. 978-987.

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12		6,117,722	9-12-00	Wuu, et al.			
		6,133,071	10-17-00	Nagai			
		6,165,383	12-26-00	Chou			
		6,221,735	4-24-01	Manley, et al.			
		6,228,694	5-8-01	Doyle, et al.			

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14		M. Khater, et al., "SiGe HBT Technology with $F_{max}/f_t = 350/300$ GHz and Gate Delay Below 3.3 ps". 2004 IEEE, 4 pages.
12		J.C. Bean, et al., "GEx Si 1-x/Si Strained-Layer Superlattice Grown by Molecular Beam Epitaxy". J. Vac. Sci. Technol. A 2(2), Apr.-June 1984, pp. 436-440.

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h		6,246,095	6-12-01	Brady, et al.			
		6,255,169	7-3-01	Li, et al.			
		6,261,964	7-17-01	Wu, et al.			
		6,265,317	7-24-01	Chiu, et al.			
✓		6,274,444	8-14-01	Wang			

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B		J.H. Van Der Herve, "Regular Articles". Journal of Applied Physics, Volume 34, No. 1, January 1963, pp. 117-122.
↓		J.W. Matthews, et al., "Defects in Epitaxial Multilayers". Journal of Crystal Growth 27 (1974), pp. 118-125.

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R		6,281,532	8-28-01	Doyle, et al.			
		6,284,623	9-4-01	Zhang, et al.			
		6,284,626	9-4-01	Kim			
		6,319,794	11-28-01	Akatsu, et al.			
		6,361,885	3-26-02	Chou			

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R		Subramanian S. Iyer, et al., "Heterojunction Bipolar Transistors Using Si-Ge Alloys". IEEE Transactions on Electron Devices, Vol. 36, No. 10, October 1989, pp. 2043-2064.						
		R.B.M. Van De Leur, et al., "Critical Thickness for Pseudomorphic Growth of Si/Ge Alloys and Superlattices". J. Appl. Phys. 64 (6), 15 September 1988, pp. 3043-3050.						

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12		6,362,082	3-26-02	Doyle, et al.			
		6,368,931	4-9-02	Kuhn, et al.			
		6,403,486	6-11-02	Lou			
		6,403,975	6-11-02	Brunner, et al.			
✓		6,406,973	6-18-02	Lee			

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12		D.C. Houghton, et al., "Equilibrium Critical Thickness for Si 1-x Ge Strained Layers on (100) Si". Appl. Phys. Lett. 56 (5), 29 January 1990, pp. 460-462.
↓		Q. Ouyang et al., "Two-Dimensional Bandgap Engineering in a Novel Si/SiGe pMOSFET with Enhanced Device Performance and Scalability". 2000 IEEE, pp. 151-154.

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8		6,461,936	10-8-02	von Ehrenwall			
		6,476,462	11-5-02	Shimizu, et al.			
		6,483,171	11-19-02	Forbes, et al.			
		6,493,497	12-10-02	Ramdani, et al.			
		6,498,358	12-24-02	Lach, et al.			

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ly		6,501,121	12-31-02	Yu, et al.			
		6,506,652	1-14-03	Jan, et al.			
		6,509,618	1-21-03	Jan, et al.			
		6,521,964	2-18-03	Jan, et al.			
		6,531,369	3-11-03	Ozkan, et al.			

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[Signature] Ron Brown

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W		6,531,740	3-11-03	Bosco, et al.			
		6,621,392	9-16-03	Volant, et al.			
		6,635,506	10-21-03	Volant, et al.			
		6,831,292	12-14-04	Currie, et al.			
		6,717,216	4-6-04	Doris, et al.			

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Docket Number (Optional)
FIS920040116US1

Application Number
10/710,244

Applicant(s)
Huillong Zhu

Filing Date
06/29/2004

Group Art Unit
2811

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